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Vishay Semiconductors

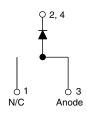
HALOGEN

FREE

HEXFRED® Ultrafast Soft Recovery Diode, 8 A



DPAK (TO-252AA)



PRIMARY CHARACTERISTICS						
I _{F(AV)}	8 A					
V _R	600 V					
V _F at I _F	1.4 V					
t _{rr} typ.	18 ns					
T _J max.	150 °C					
Package	DPAK (TO-252AA)					
Circuit configuration	Single					

FEATURES

- Ultrafast recovery time
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- · Guaranteed avalanche
- · Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI / RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Cathode to anode voltage	V_{RRM}		600	V				
Maximum continuous forward current	I _F	T _C = 100 °C	8					
Single pulse forward current	I _{FSM}		60	Α				
Peak repetitive forward current	I _{FRM}		24					
Maximum power dissipation	P _D	T _C = 100 °C	14	W				
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-		
Forward voltage		I _F = 8 A	See fig. 1	-	1.4	1.7	V
	V _F	I _F = 16 A		-	1.7	2.1	
		I _F = 8 A, T _J = 125 °C		-	1.4	1.7	
Maximum reverse		V _R = V _R rated		-	0.3	5.0	
leakage current	I _R	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated		-	100	500	μA
Junction capacitance	C _T	V _R = 200 V See fig. 3		-	10	25	pF
Series inductance	L _S	Measured lead to lead 5 mm from page	ckage body	-	8.0	-	nH



DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	18	-		
Reverse recovery time	t _{rr}	T _J = 25 °C	$I_F = 8 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	37	55	ns	
		T _J = 125 °C		-	55	90		
Peak recovery current	I _{RRM}	T _J = 25 °C		-	3.5	5.0	Α	
		T _J = 125 °C		-	4.5	8.0		
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	65	138	nC	
neverse recovery charge		T _J = 125 °C		-	124	360	10	
Rate of fall of recovery current	dl _{(rec)M} /dt	T _J = 25 °C		-	240	-	A/µs	
		T _J = 125 °C		-	210	-	ΑνμS	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	150	°C		
Thermal resistance, junction to case	R _{thJC}		-	-	3.5	°C/W		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	C/VV		
Weight			-	2.0	-	g		
vveigni			-	0.07	-	oz.		
Marking device		Case style DPAK (TO-252AA)		HFA08	SD60S			





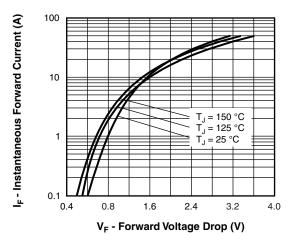


Fig. 1 - Typical Forward Voltage Drop Characteristics

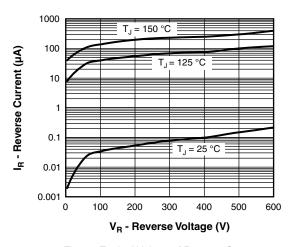


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

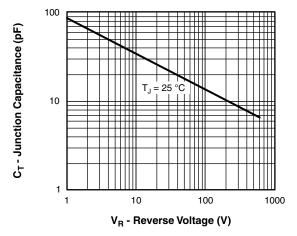


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

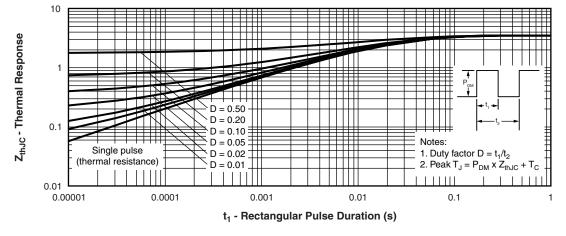


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



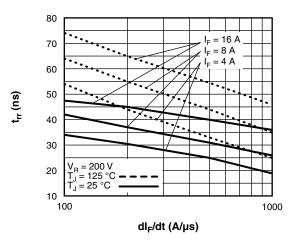


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

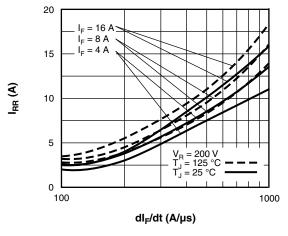


Fig. 6 - Typical Recovery Current vs. dl_F/dt

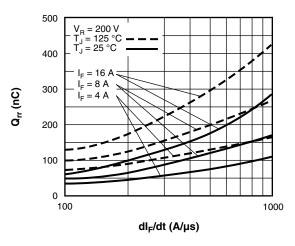


Fig. 7 - Typical Stored Charge vs. dl_F/dt

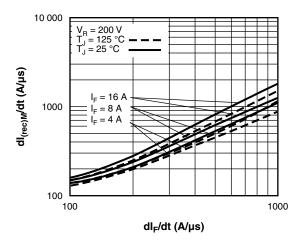


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

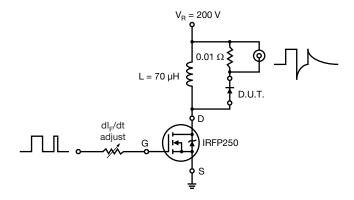
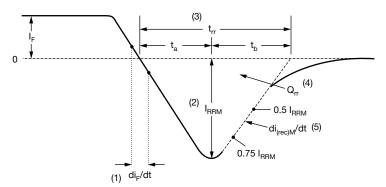


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

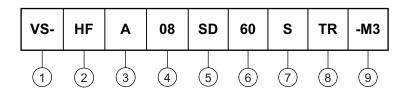
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

3 - Electron irradiated

4 - Current rating (08 = 8 A)

5 - D-PAK

6 - Voltage rating (60 = 600 V)

7 - S = D-PAK

8 - • TR = tape and reel

• R = tape and reel (right oriented)

• L = tape and reel (left oriented)

9 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

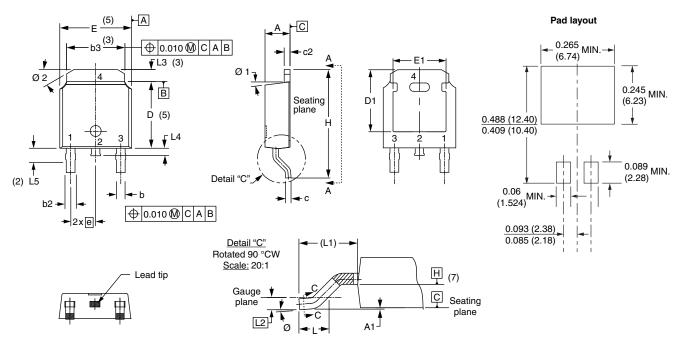
ORDERING INFORMATION (Example)							
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION					
VS-HFA08SD60S-M3	75	Antistatic plastic tube					
VS-HFA08SD60STR-M3	2000	13" diameter reel					
VS-HFA08SD60SL-M3	3000	13" diameter reel					
VS-HFA08SD60SR-M3	3000	13" diameter reel					

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95627					
Part marking information	www.vishay.com/doc?95176					
Packaging information	www.vishay.com/doc?95033					



D-PAK (TO-252AA) "M"

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	INCHES		SY
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	31
Α	2.18	2.39	0.086	0.094		
A1	-	0.13	-	0.005		
b	0.64	0.89	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215	3	
С	0.46	0.61	0.018	0.024		
c2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245	5	
D1	5.21	-	0.205	-	3	
Е	6.35	6.73	0.250	0.265	5	
E1	4.32	-	0.170	-	3	

SYMBOL	MILLIMETERS		INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
е	2.29 BSC		0.090	BSC	
Н	9.40	10.41	0.370	0.410	
L	1.40	1.78	0.055	0.070	
L1	2.74 BSC		0.108 REF.		
L2	0.51 BSC		0.020 BSC		
L3	0.89	1.27	0.035	0.035 0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	2
Ø	0°	10°	0°	10°	
Ø1	0°	15°	0°	15°	
Ø2	25°	35°	25°	35°	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension uncontrolled in L5
- (3) Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- (5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (6) Dimension b1 and c1 applied to base metal only
- (7) Datum A and B to be determined at datum plane H
- (8) Outline conforms to JEDEC® outline TO-252AA



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